

MOSFET - Power, Dual N-Channel

100 V, 26 mΩ, 28 A

NVMFD027N10MCL

Features

- Small Footprint (5x6 mm) for Compact Design
- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- AEC-Q101 Qualified and PPAP Capable
- NVMFD027N10MCL – Wettable Flank Products
- These Devices are Pb-Free, Halogen Free/BFR Free, Beryllium Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V_{DSS}	100	V
Gate-to-Source Voltage			V_{GS}	± 20	V
Continuous Drain Current $R_{\theta JC}$ (Note 1)	Steady State	$T_C = 25^{\circ}\text{C}$	I_D	28	A
		$T_C = 100^{\circ}\text{C}$		20	
Power Dissipation $R_{\theta JC}$ (Note 1)		$T_C = 25^{\circ}\text{C}$	P_D	46	W
		$T_C = 100^{\circ}\text{C}$		23	
Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2)	Steady State	$T_A = 25^{\circ}\text{C}$	I_D	7.4	A
		$T_A = 100^{\circ}\text{C}$		5.2	
Power Dissipation $R_{\theta JA}$ (Notes 1, 2)		$T_A = 25^{\circ}\text{C}$	P_D	3.1	W
		$T_A = 100^{\circ}\text{C}$		1.6	
Pulsed Drain Current	$T_A = 25^{\circ}\text{C}$, $t_p = 10\text{ }\mu\text{s}$		I_{DM}	115	A
Operating Junction and Storage Temperature Range			T_J , T_{stg}	-55 to +175	$^{\circ}\text{C}$
Source Current (Body Diode)			I_S	35	A
Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 1.3\text{ A}$)			E_{AS}	154	mJ
Lead Temperature Soldering Reflow for Soldering Purposes (1/8" from case for 10 s)			T_L	260	$^{\circ}\text{C}$

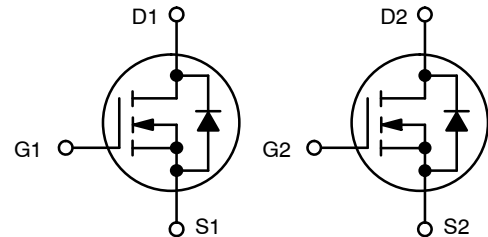
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case – Steady State (Note 1)	$R_{\theta JC}$	3.29	$^\circ\text{C/W}$
Junction-to-Ambient – Steady State (Note 2)	$R_{\theta JA}$	48	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface-mounted on FR4 board using 1 in² pad size, 2 oz. Cu pad.

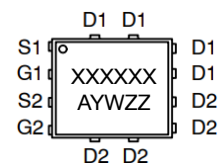
$V_{(BR)DSS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
100 V	26 mΩ @ 10 V	28 A
	35 mΩ @ 4.5 V	



DUAL N-CHANNEL



MARKING DIAGRAM



XXXXXX = Specific Device Code
 A = Assembly Location
 Y = Year
 W = Work Week
 ZZ = Lot Traceability

ORDERING INFORMATION

Device	Package	Shipping†
NVMFD027N10MCLT1G	DFN8 (Pb-Free)	1500 / Tape & Reel
NVMFWD027N10MCLT1G (Wettable Flanks)		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NVMFD027N10MCL

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	100			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			50		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 100 V	T _J = 25°C		1.0	μA
			T _J = 125°C		100	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = 20 V			100	nA

ON CHARACTERISTICS

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 38 μA	1		3	V
Threshold Temperature Coefficient	V _{GS(TH)} /T _J			-5.4		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 7 A		21	26	mΩ
		V _{GS} = 4.5 V, I _D = 5 A		28	35	
Forward Transconductance	g _{FS}	V _{DS} = 10 V, I _D = 7 A		27		S

CHARGES & CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 50 V		720		pF
Output Capacitance	C _{OSS}			300		
Reverse Transfer Capacitance	C _{RSS}			6		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 50 V, I _D = 7 A		5.5		nC
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 50 V, I _D = 7 A		11		
Threshold Gate Charge	Q _{G(TH)}			1.1		
Gate-to-Source Charge	Q _{GS}			2		
Gate-to-Drain Charge	Q _{GD}			1.4		
Plateau Voltage	V _{GP}			2.5		V

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 10 V, V _{DS} = 50 V, I _D = 7 A, R _G = 6 Ω		7		ns
Rise Time	t _r			2.5		
Turn-Off Delay Time	t _{d(OFF)}			19		
Fall Time	t _f			3.2		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 7 A	T _J = 25°C		0.84	1.3	V
			T _J = 125°C		0.73		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 3 A		28			ns
Reverse Recovery Charge	Q _{RR}			17			nC
Charge Time	t _a			13.9			ns
Discharge Time	t _b			14.2			ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS

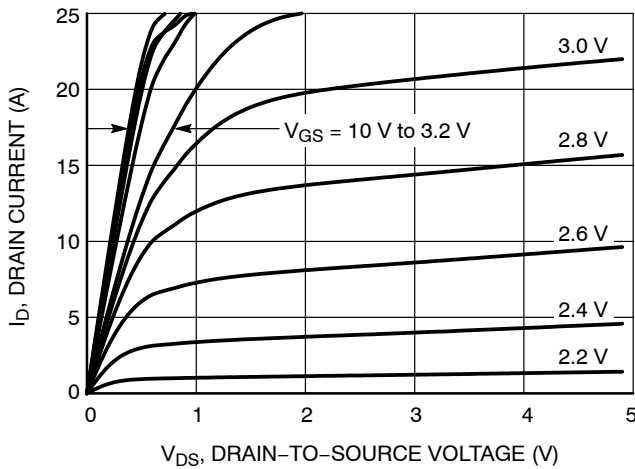


Figure 1. On-Region Characteristics

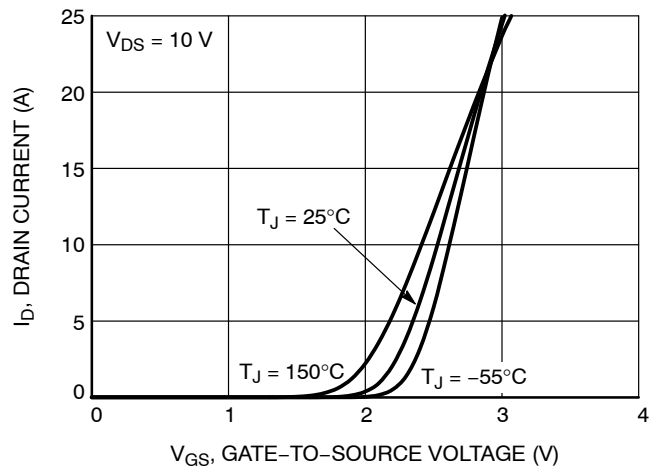


Figure 2. Transfer Characteristics

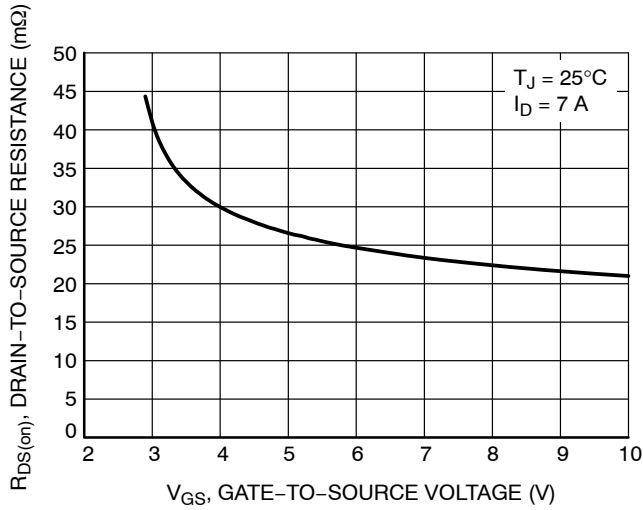


Figure 3. On-Resistance vs. Gate-to-Source Voltage

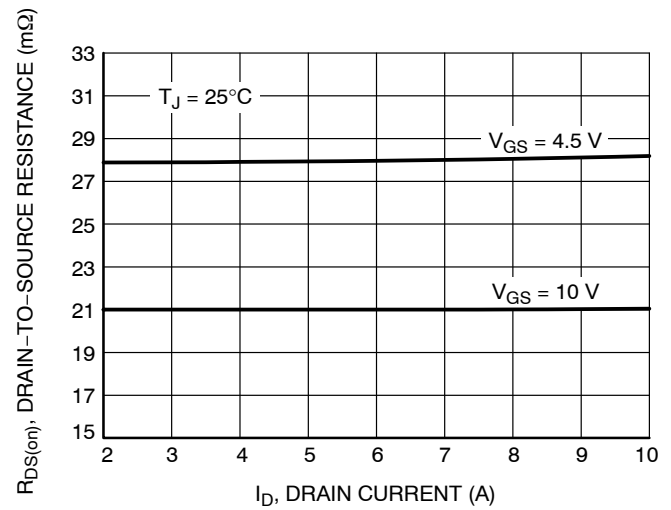


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

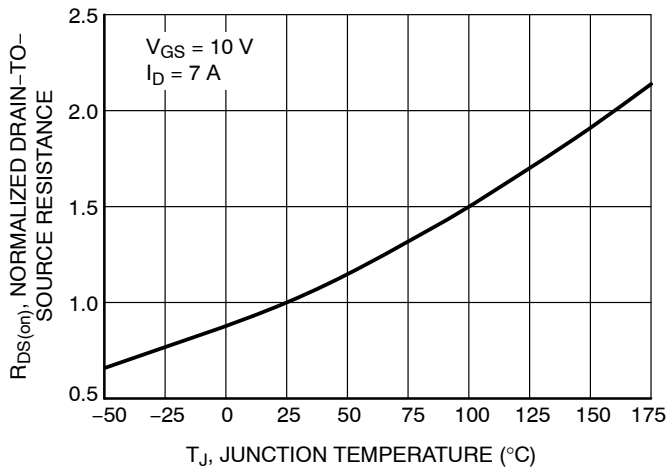


Figure 5. On-Resistance Variation with Temperature

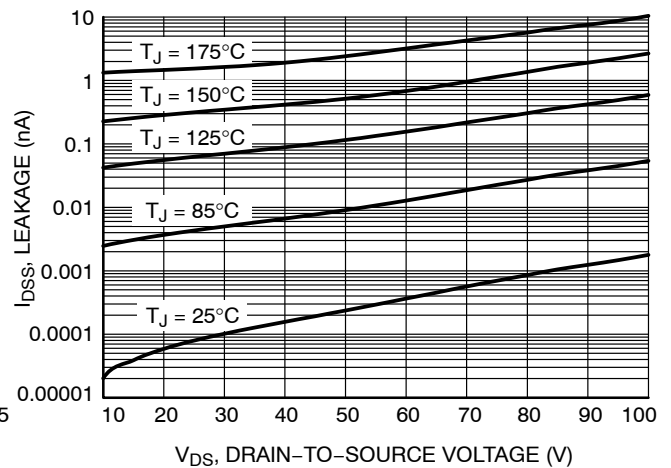


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

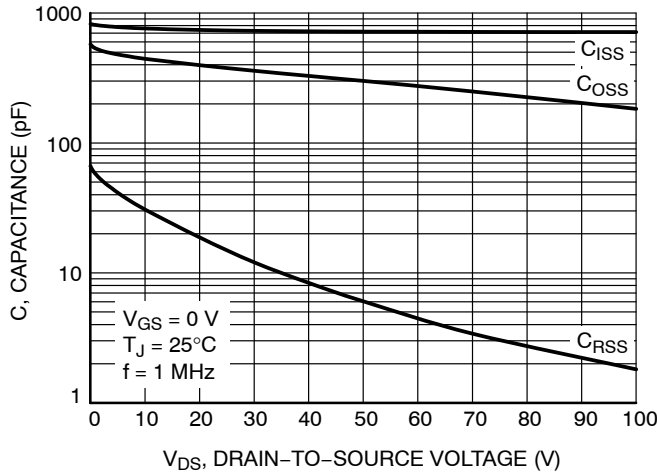


Figure 7. Capacitance Variation

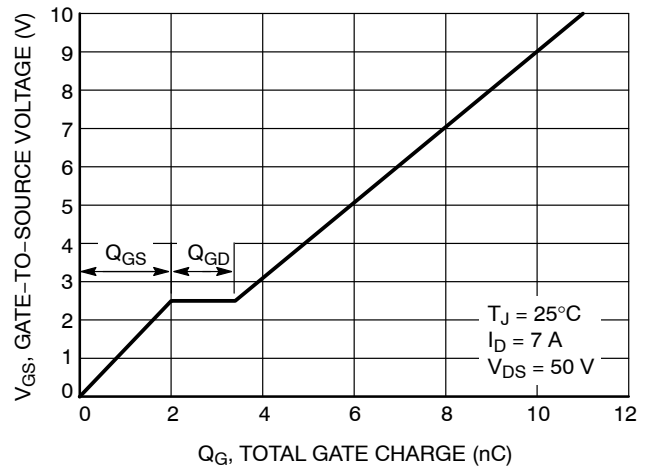


Figure 8. Gate-to-Source Voltage vs. Total Charge

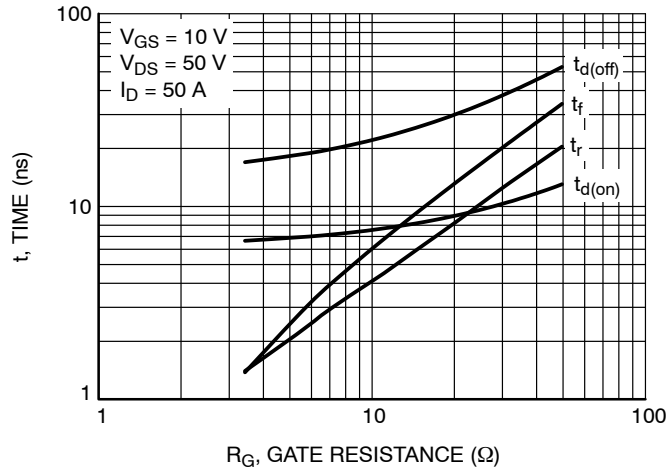


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

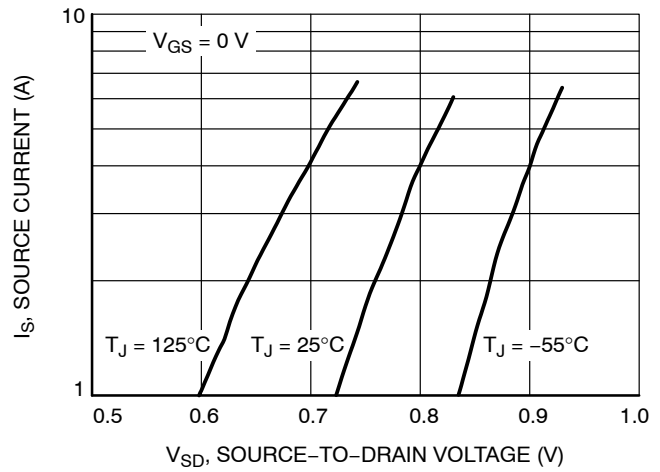


Figure 10. Diode Forward Voltage vs. Current

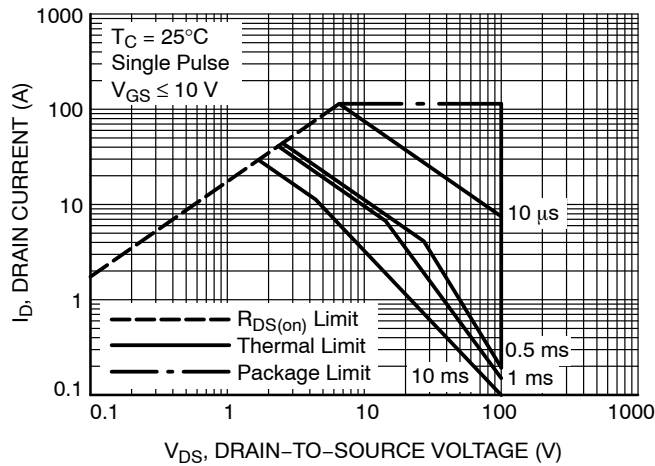


Figure 11. Maximum Rated Forward Biased Safe Operating Area

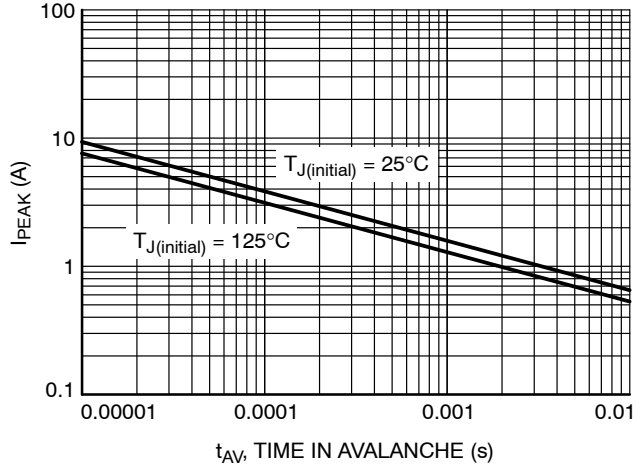


Figure 12. Maximum Drain Current vs. Time in Avalanche

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TYPICAL CHARACTERISTICS

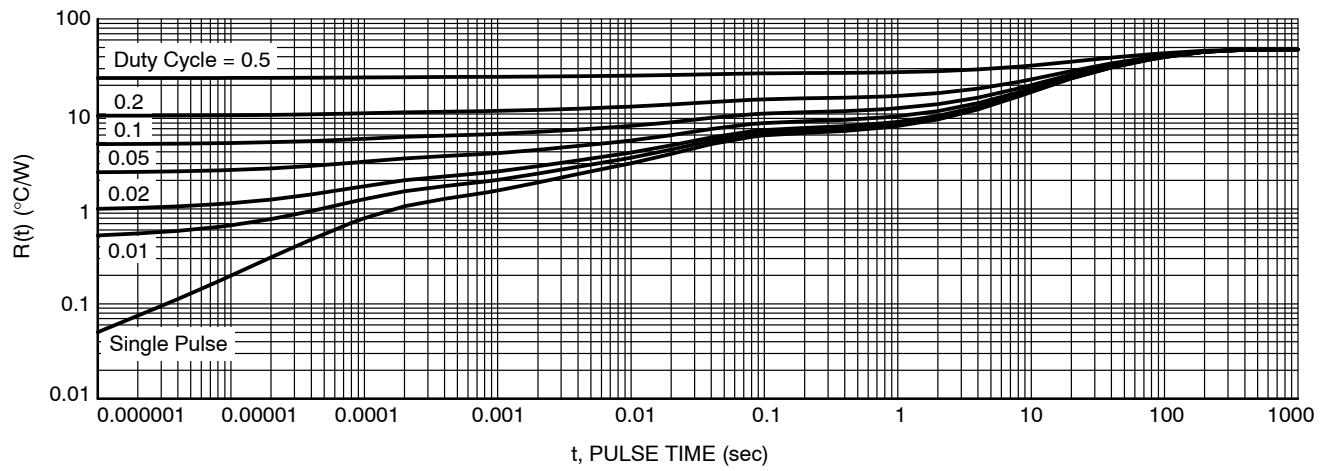


Figure 13. Transient Thermal Impedance

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